

## VHF power transistor

BLV11

### DESCRIPTION

N-P-N silicon planar epitaxial transistor intended for use in class-A, B and C operated mobile, h.f. and v.h.f. transmitters with a nominal supply voltage of 13,5 V. The transistor is resistance stabilized and is guaranteed to withstand severe load mismatch conditions with a supply over-voltage to 16,5 V.

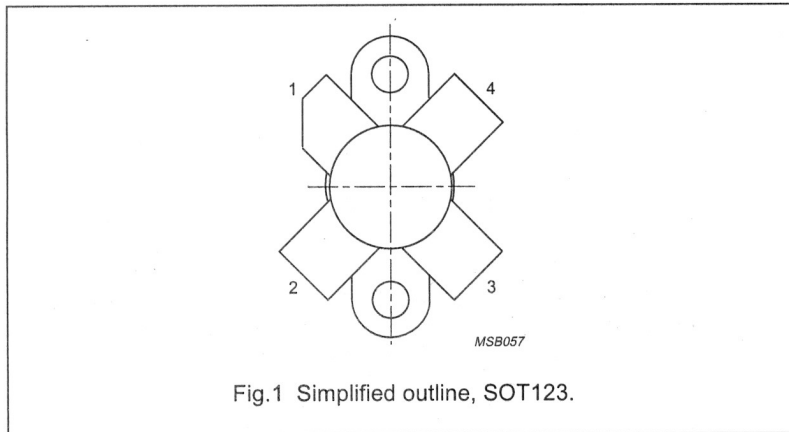
It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

### QUICK REFERENCE DATA

R.F. performance up to  $T_h = 25\text{ }^\circ\text{C}$  in an unneutralized common-emitter class-B circuit

MODE OF OPERATION	$V_{CE}$ V	f MHz	$P_L$ W	$G_p$ dB	$\eta$ %	$\bar{z}_i$ $\Omega$	$\bar{Y}_L$ mS
c.w.	13,5	175	15	> 8,0	> 60	$2,3 + j2,2$	$130 - j4,4$
c.w.	12,5	175	15	typ. 7,5	typ. 67	-	-

### PIN CONFIGURATION



### PINNING

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

**PRODUCT SAFETY** This device incorporates beryllium oxide, the dust of which is toxic. The device is entirely safe provided that the BeO disc is not damaged.